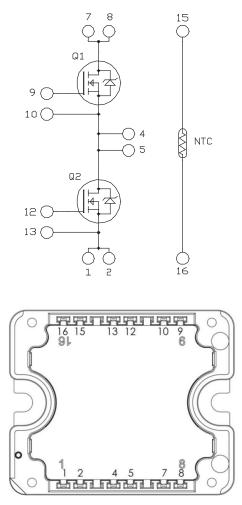


# Phase Leg SiC MOSFET Power Module

### **Product Overview**

The MSCSM120AM16T1AG device is a phase leg 1200V, 173A silicon carbide (SiC) MOSFET power module.



#### Notes:

- Pins 1/2; 4/5; 7/8 must be shorted together.
- All ratings at T<sub>J</sub> = 25 °C, unless otherwise specified.

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

### Features

The following are key features of the MSCSM120AM16T1AG device:

- SiC Power MOSFET
  - Low R<sub>DS(on)</sub>
  - High temperature performance
- Very low stray inductance
- Kelvin source for an easy drive
- Internal thermistor for temperature monitoring
- Aluminum Nitride (AIN) substrate for improved thermal performance

### **Benefits**

The following are the benefits of MSCSM120AM16T1AG device:

- High power and efficiency converters and inverters
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

### Application

The MSCSM120AM16T1AG device is designed for the following applications:

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- EV motor and traction drive

## 1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120AM16T1AG device.

### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120AM16T1AG device.

### Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Parameter N		Unit
V <sub>DSS</sub>	Drain-Source voltage	n-Source voltage 1		V
I <sub>D</sub>	Continuous drain current	T <sub>C</sub> = 25 °C	173 <sup>1</sup>	A
		T <sub>C</sub> = 80 °C	138 <sup>1</sup>	
I <sub>DM</sub>	Pulsed drain current		350	
V <sub>GS</sub>	Gate-Source voltage		-10/23	V
R <sub>DS(on)</sub>	Drain-Source ON resistance	Drain-Source ON resistance		mΩ
P <sub>D</sub>	Power dissipation	T <sub>C</sub> = 25 °C	745	W

#### Note:

1. SiC MOSFET device specification, but the output current must be limited due to the size of the power connectors.

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120AM16T1AG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0V V <sub>DS</sub> = 1200V		—	20	200	μA
R <sub>DS(on)</sub>	Drain-Source on	V <sub>GS</sub> = 20V	T <sub>J</sub> = 25 °C		12.5	16	mΩ
	resistance	I <sub>D</sub> = 80A	T <sub>J</sub> = 175 °C		20	_	
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 6 mA$		1.8	2.8	—	V
I <sub>GSS</sub>	Gate–Source leakage current	$V_{GS}$ = 20V; $V_{DS}$ = 0V		_	_	200	nA

**Electrical Specifications** 

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120AM16T1AG device.

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0V		—	6040	—	pF
C <sub>oss</sub>	Output capacitance	V <sub>DS</sub> = 1000V		—	540	—	-
C <sub>rss</sub>	Reverse transfer capacitance	f = 1 MHz		_	50	_	
Qg	Total gate charge	V <sub>GS</sub> = -5V/20V		-	464	—	nC
Q <sub>gs</sub>	Gate-Source charge	V <sub>Bus</sub> = 800V		-	82	_	
Q <sub>gd</sub>	Gate-Drain charge	I <sub>D</sub> = 80A		—	100	—	
T <sub>d(on)</sub>	Turn-on delay time	V <sub>GS</sub> = -5V/20V		_	30	—	ns
Tr	Rise time	V <sub>Bus</sub> = 600V		—	30	—	
T <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 100A		_	50	_	
T <sub>f</sub>	Fall time	$R_{G(on)} = 4\Omega$ $R_{G(off)} = 2.4\Omega$			25	—	
Eon	Turn-on energy	V <sub>GS</sub> = -5V/20V	T <sub>J</sub> = 150 °C	_	2.4	_	mJ
E <sub>off</sub>	Turn-off energy	$V_{Bus} = 600V$ $I_{D} = 100A$ $R_{G(on)} = 4\Omega$ $R_{G(off)} = 2.4\Omega$		-	1.3	_	
R <sub>Gint</sub>	Internal gate resistance		-	2.94	-	Ω	
R <sub>thJC</sub>	Junction-to-case therm	nal resistance		—	—	0.2	°C/W

### Table 1-3. Dynamic Characteristics

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120AM16T1AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>SD</sub>	Diode forward voltage	V <sub>GS</sub> = 0V; I <sub>SD</sub> = 80A		4	_	V
		$V_{GS} = -5V; I_{SD} = 80A$		4.2		
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 80A; V <sub>GS</sub> = -5V		90		ns
Q <sub>rr</sub>	Reverse recovery charge	V <sub>R</sub> = 800V; di <sub>F</sub> /dt = 2000 A/µs		1100		nC
I <sub>rr</sub>	Reverse recovery current		_	27		А

### **Electrical Specifications**

### 1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120AM16T1AG device.

Symbol	Characteristics	Characteristics				Unit
V <sub>ISOL</sub>	RMS isolation voltage, any terminal	RMS isolation voltage, any terminal to case t =1 min, 50 Hz/60 Hz			—	V
TJ	Operating junction temperature rang	Operating junction temperature range			175	°C
T <sub>JOP</sub>	Recommended junction temperature	Recommended junction temperature under switching conditions			T <sub>Jmax</sub> –25	
T <sub>STG</sub>	Storage temperature range	Storage temperature range			125	
T <sub>C</sub>	Operating case temperature	Operating case temperature			125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight				80	g

### Table 1-5. Thermal and Package Characteristics

The following table lists the temperature sensor NTC of the MSCSM120AM16T1AG device.

### Table 1-6. Temperature Sensor NTC

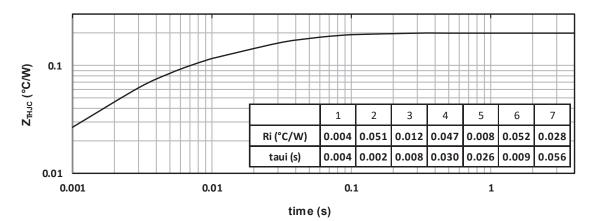
Symbol	Characteristic		Min.	Тур.	Max.	Unit
R <sub>25</sub>	Resistance at 25 °C		_	50	—	kΩ
$\Delta R_{25}/R_{25}$	—	—		5	_	%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15K	—		3952		К
ΔΒ/Β	—	T <sub>C</sub> = 100 °C		4	_	%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

**Note:** See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

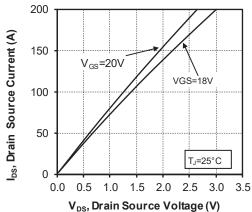
### 1.3 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120AM16T1AG device.

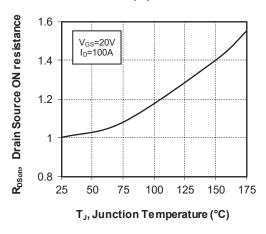


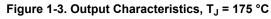
### Figure 1-1. Maximum Thermal Impedance

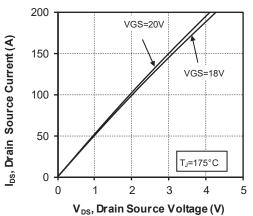




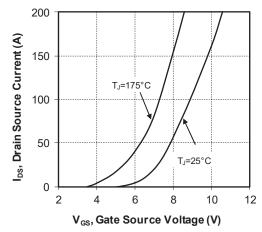




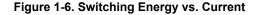


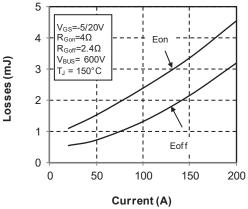


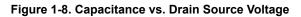


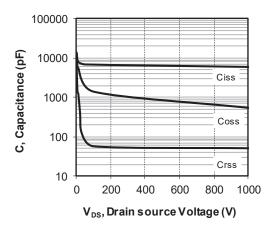


**Electrical Specifications** 











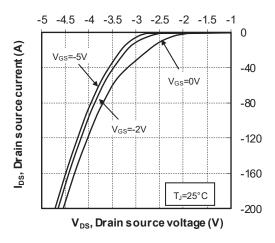


Figure 1-7. Switching Energy vs. Rg

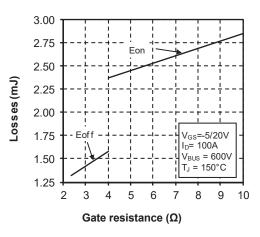


Figure 1-9. Gate Charge vs. Gate Source Voltage

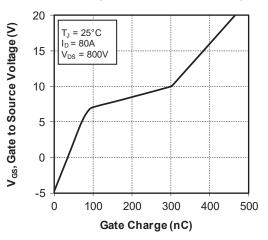
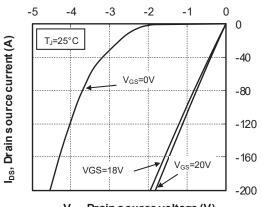
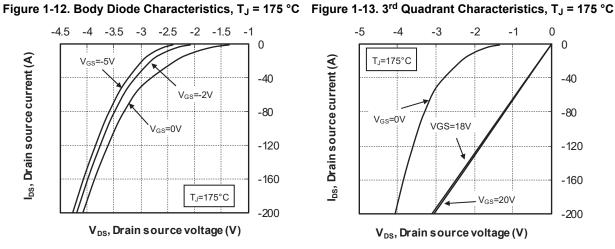


Figure 1-11. 3<sup>rd</sup> Quadrant Characteristics, T<sub>J</sub> = 25 °C



V<sub>DS</sub>, Drain source voltage (V)

### **Electrical Specifications**



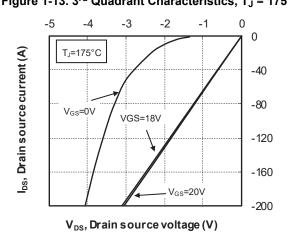
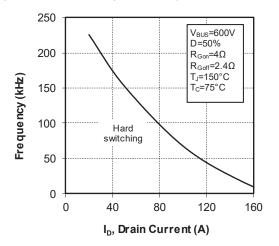


Figure 1-14. Operating Frequency vs Drain Current



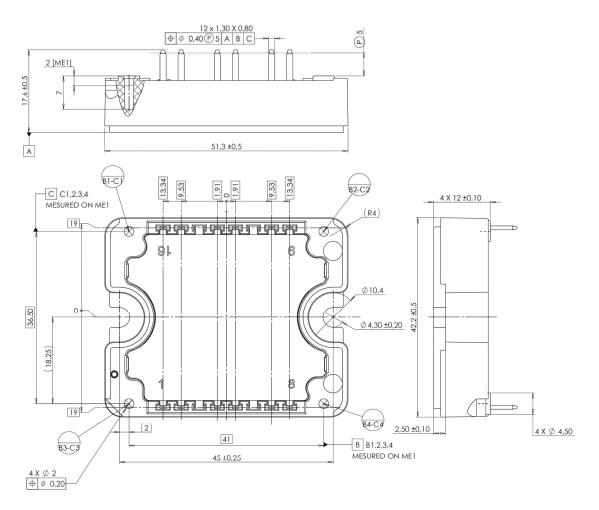
## 2. Package Specifications

The following section shows the package specification of the MSCSM120AM16T1AG device.

### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120AM16T1AG device. The dimensions in the following figure are in millimeters.

### Figure 2-1. Package Outline Drawing



**Note:** See AN3500A - Mounting instructions for SP1F and SP3F Power Modules for more information.

# **Revision History**

# 3. Revision History

Revision	Date	Description
A	06/2022	Initial Revision

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